

# MOSFET – Power, Single N-Channel 100 V, 14 mΩ, 46 A

## NVMYS016N10MCL

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	$I_D$	A
	$T_C = 100^\circ\text{C}$		
Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	$P_D$	W
	$T_C = 100^\circ\text{C}$		
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	$T_A = 25^\circ\text{C}$	$I_D$	A
	$T_A = 100^\circ\text{C}$		
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	$T_A = 25^\circ\text{C}$	$P_D$	W
	$T_A = 100^\circ\text{C}$		
Pulsed Drain Current	$T_A = 25^\circ\text{C}$ , $t_p = 10\ \mu\text{s}$	$I_{DM}$	A
Operating Junction and Storage Temperature Range	$T_J$ , $T_{stg}$	-55 to +175	°C
Source Current (Body Diode)	$I_S$	49	A
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 2.2\text{ A}$ )	$E_{AS}$	358	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	°C

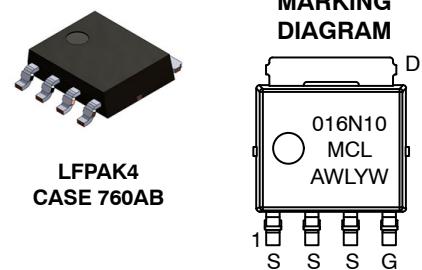
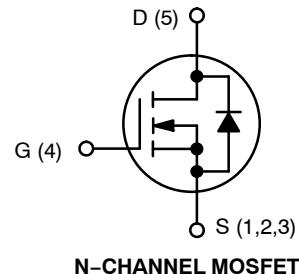
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	2.35	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	41	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in<sup>2</sup> pad size, 2 oz. Cu pad.

$V_{(BR)DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
100 V	14 mΩ @ 10 V	46 A
	20 mΩ @ 4.5 V	



016N10MCL = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NVMYS016N10MCL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA, ref to 25°C		60		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V	T <sub>J</sub> = 25°C		1	μA
			T <sub>J</sub> = 125°C		100	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			100	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 64 μA	1		3	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	I <sub>D</sub> = 64 μA, ref to 25°C		-5.6		mV/°C
Drain-to-Source On Resistance	R <sub>DSS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A		11.5	14	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9 A		16	20	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A		42		S
Gate-Resistance	R <sub>G</sub>	T <sub>A</sub> = 25°C		1.2		Ω

### CHARGES & CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 50 V		1250		pF
Output Capacitance	C <sub>OSS</sub>			460		
Reverse Transfer Capacitance	C <sub>rss</sub>			8		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 11 A		9.0		nC
Total Gate Charge	Q <sub>G(TOT)</sub>			19		
Threshold Gate Charge	Q <sub>G(TH)</sub>			2.1		
Gate-to-Source Charge	Q <sub>GS</sub>			3.7		
Gate-to-Drain Charge	Q <sub>GD</sub>			2.0		
Plateau Voltage	V <sub>GP</sub>			2.8		V

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 50 V, I <sub>D</sub> = 11 A, R <sub>G</sub> = 6 Ω		10		ns
Rise Time	t <sub>r</sub>			3.4		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			26		
Fall Time	t <sub>f</sub>			4.2		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 11 A	T <sub>J</sub> = 25°C		0.84	1.3	V
			T <sub>J</sub> = 125°C		0.72		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 6 A			34		ns
Reverse Recovery Charge	Q <sub>RR</sub>				24		
Charge Time	t <sub>a</sub>				16		
Discharge Time	t <sub>b</sub>				17		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

## TYPICAL CHARACTERISTICS

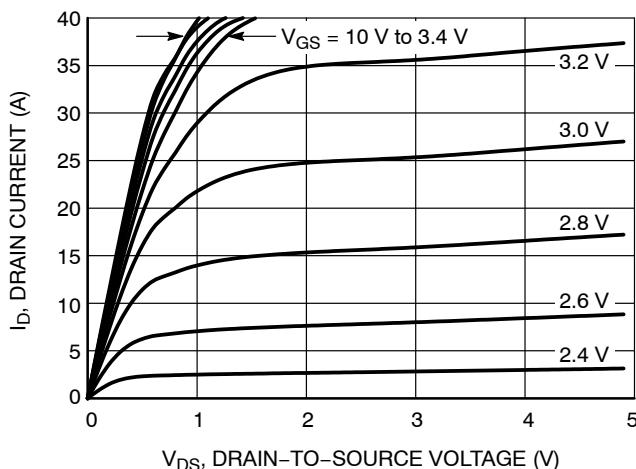


Figure 1. On-Region Characteristics

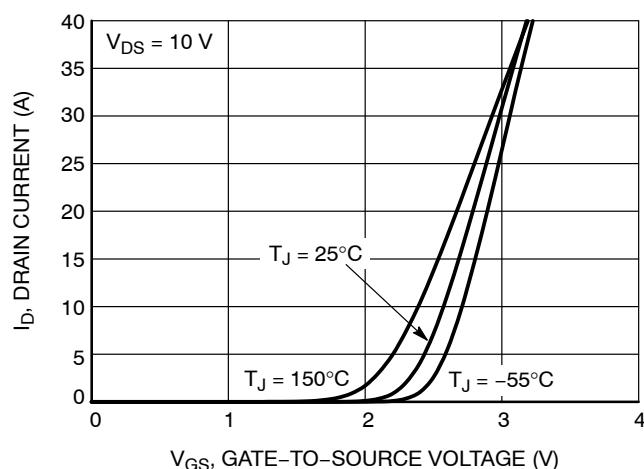


Figure 2. Transfer Characteristics

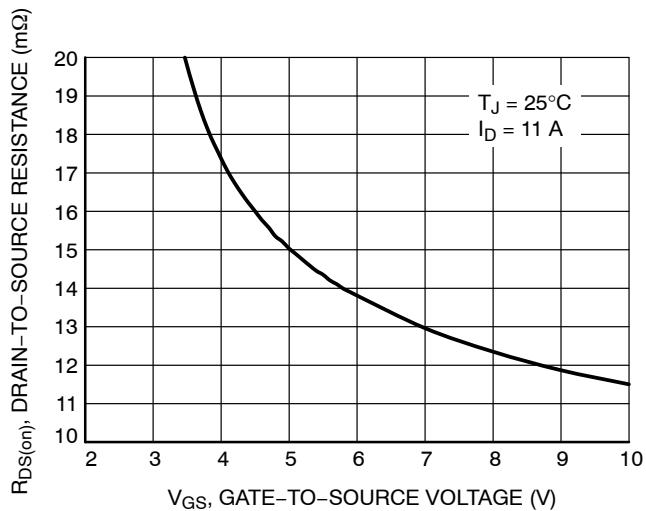


Figure 3. On-Resistance vs. Gate-to-Source Voltage

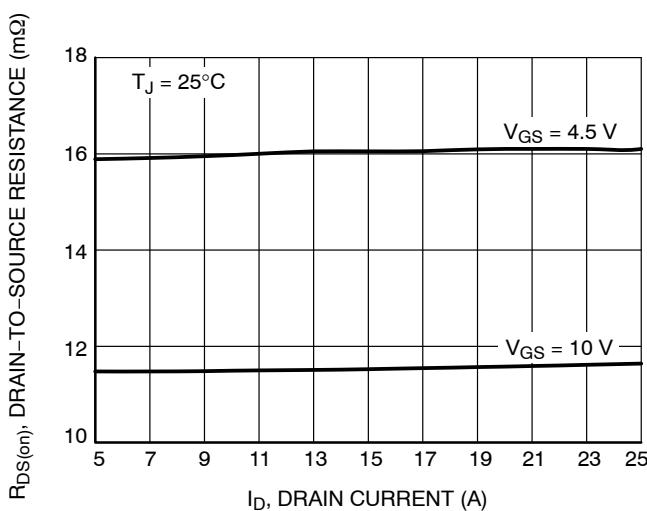


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

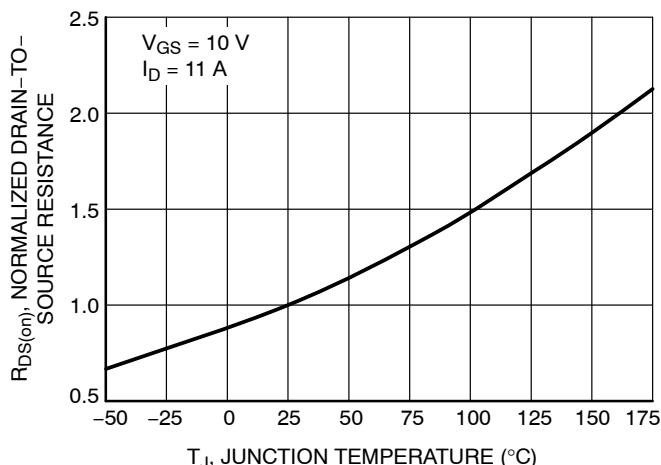


Figure 5. On-Resistance Variation with Temperature

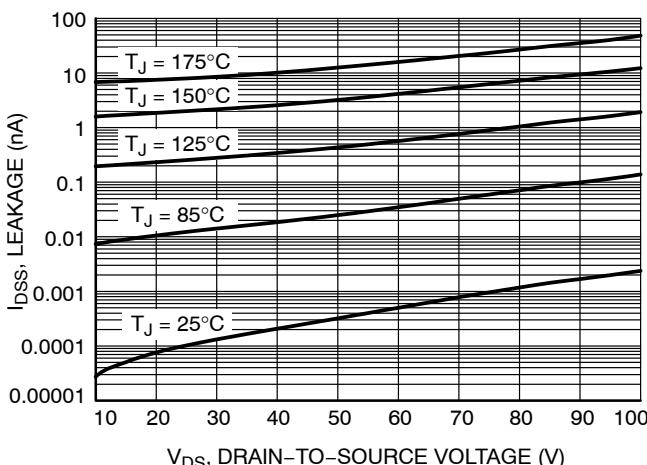


Figure 6. Drain-to-Source Leakage Current vs. Voltage

## TYPICAL CHARACTERISTICS

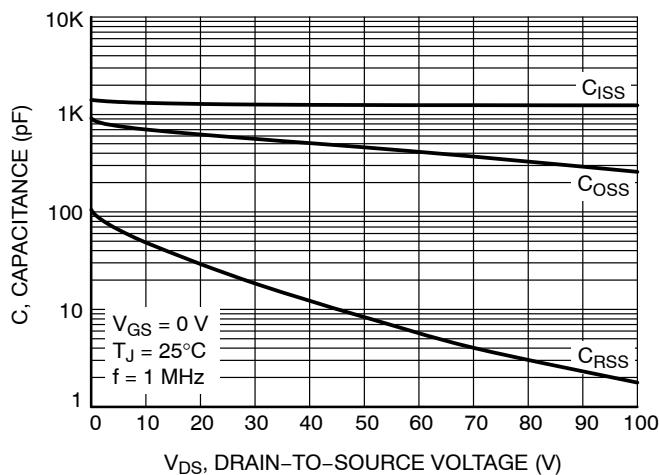


Figure 7. Capacitance Variation

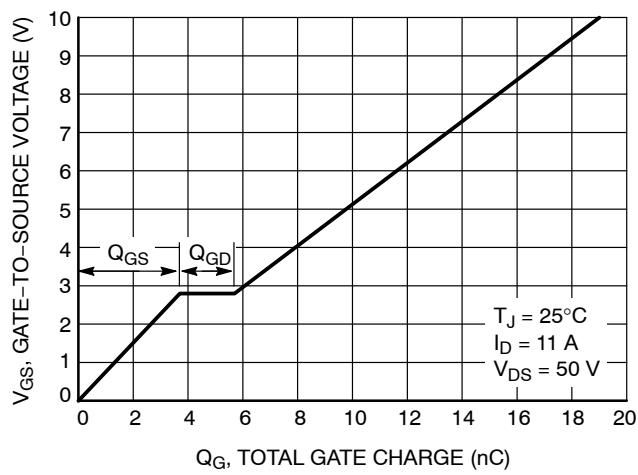


Figure 8. Gate-to-Source Voltage vs. Total Charge

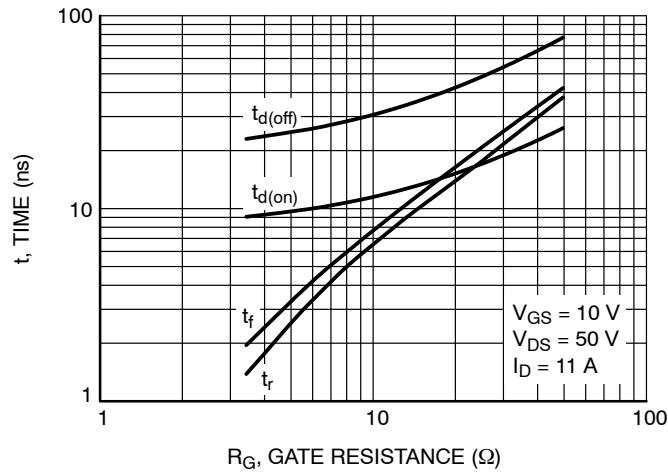


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

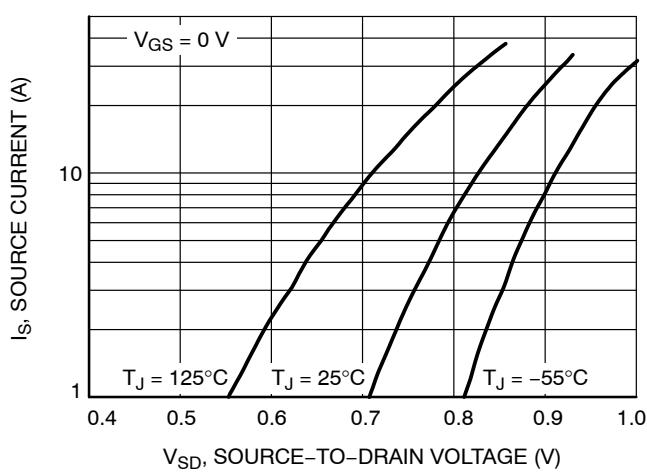


Figure 10. Diode Forward Voltage vs. Current

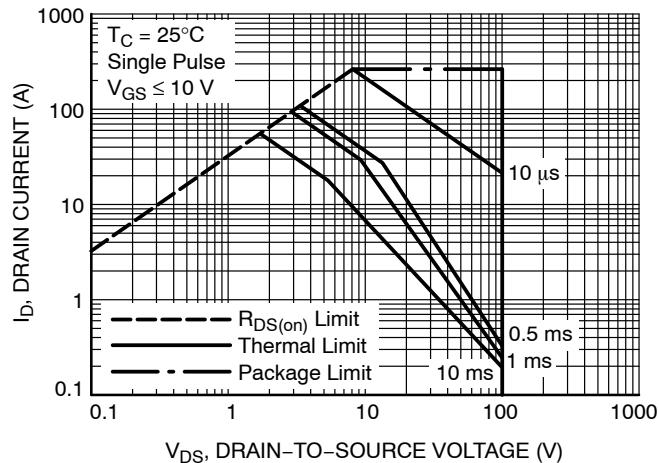


Figure 11. Maximum Rated Forward Biased Safe Operating Area

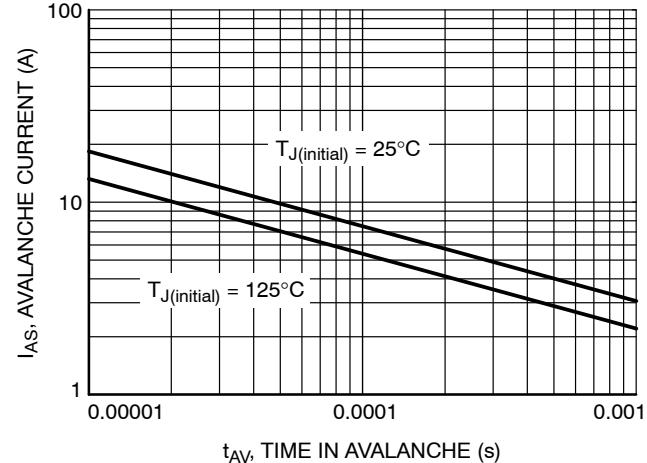
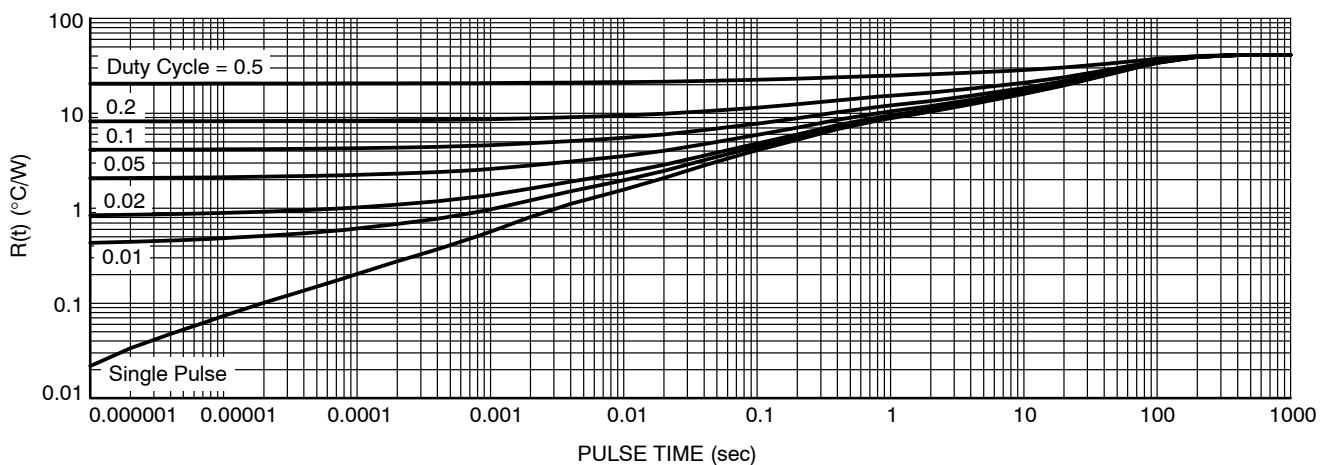


Figure 12. Maximum Drain Current vs. Time in Avalanche

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## TYPICAL CHARACTERISTICS



**Figure 13. Transient Thermal Impedance**

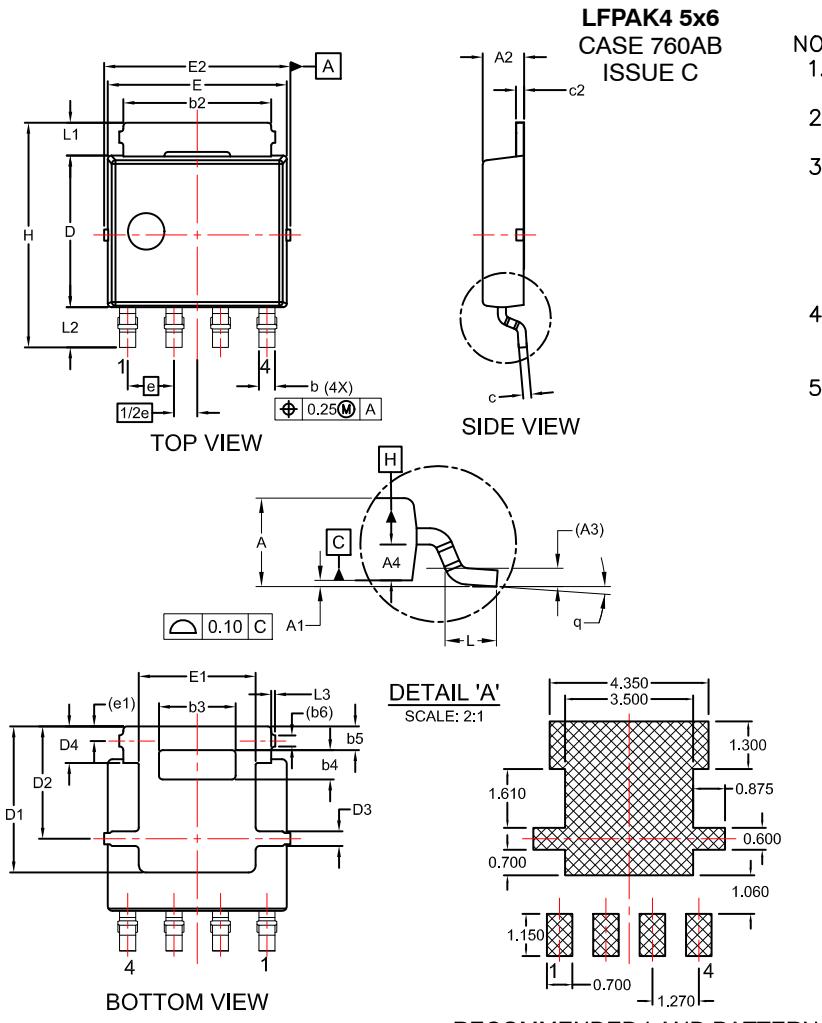
## DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NVMYS016N10MCLTWG	016N10MCL	LFPAK4 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## PACKAGE DIMENSIONS



\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 REF		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
b6	0.31 REF		
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27 BSC		
1/2e	0.635 BSC		
e1	0.40 REF		
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.90	1.10	1.30
L3	0.00	0.10	0.20
q	0°	4°	8°

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